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OCT 23 2001
TECHNOLOGY CENTER 2800

In re Application of:

Cyprian E. Uzoh et al.

Serial No.: 09/611,955

Art Unit: 2818

Filed: July 6, 2000

Examiner: Vu, H.

For: Method to Selectively Fill
Recesses with Conductive
Metal

Atty Docket: FIS919970205US2

RESPONSE AND AMENDMENT UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated July 19, 2001, please amend the
above-identified application as follows:

IN THE SPECIFICATION:

Please amend the Specification as follows:

Page 7, first paragraph under "Best and Various Modes for Carrying Out Invention":

In accordance with the present invention, recesses 2 such as troughs and vias are
provided on at least one major surface of a semiconductor substrate 13. Typical
semiconductor substrates include silicon and group III-V semiconductors. Electrical
insulation 3 is provided over the major surface and in the recesses such as silicon